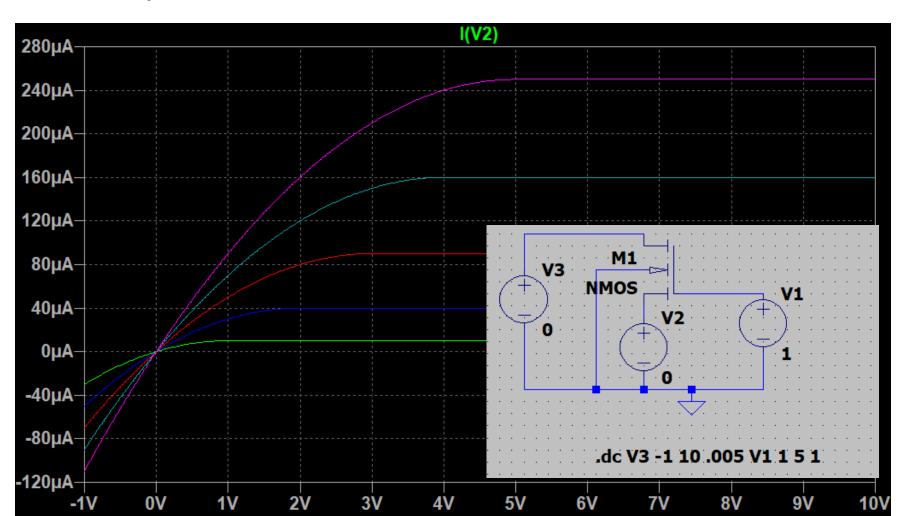
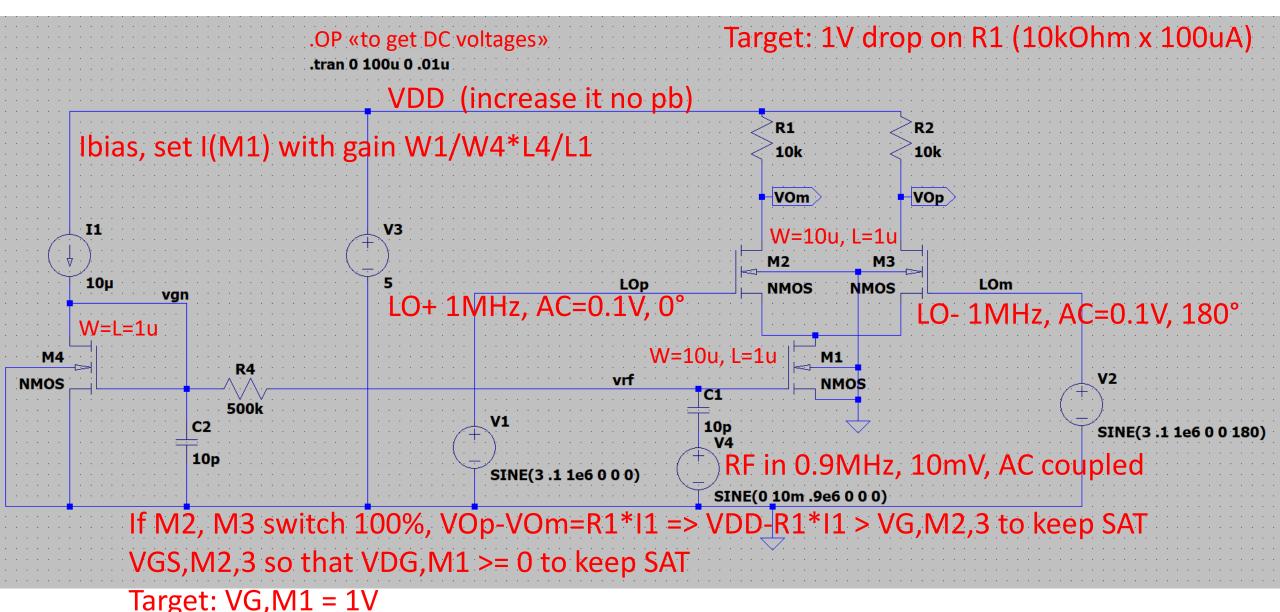


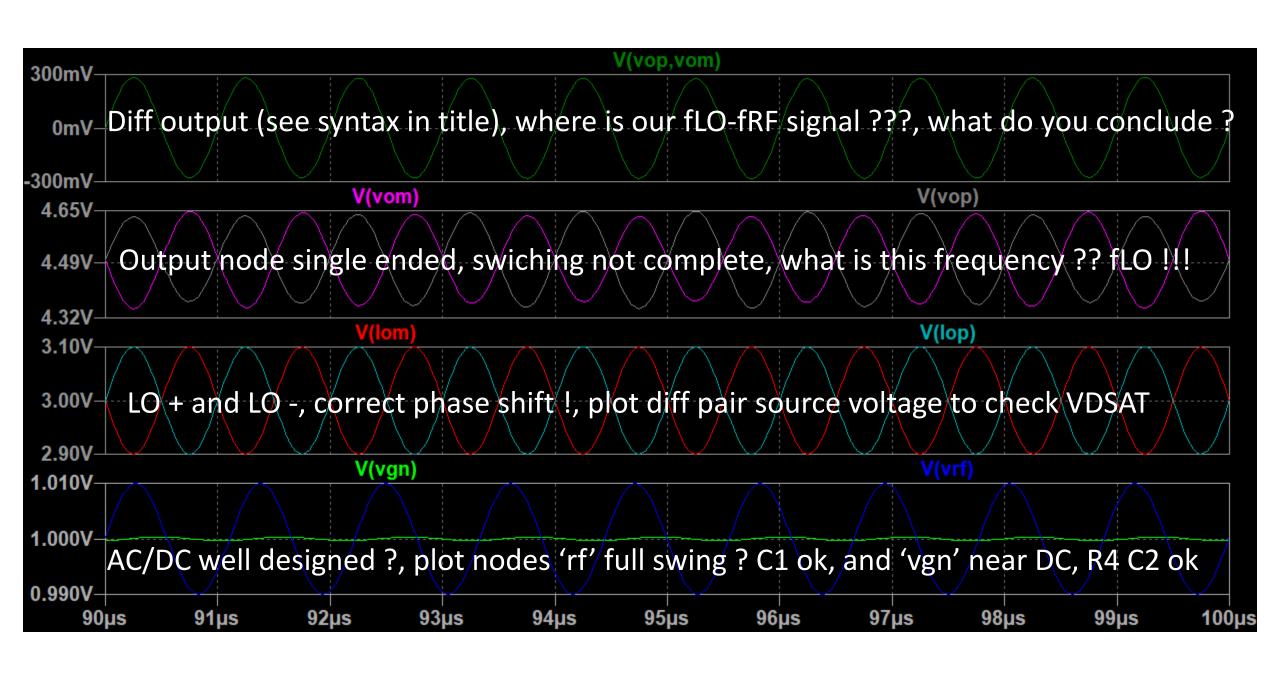
Determine VDSAT (normally (VG-VT)/n) Redo this with EKV 0.18um model VDD=1.8V

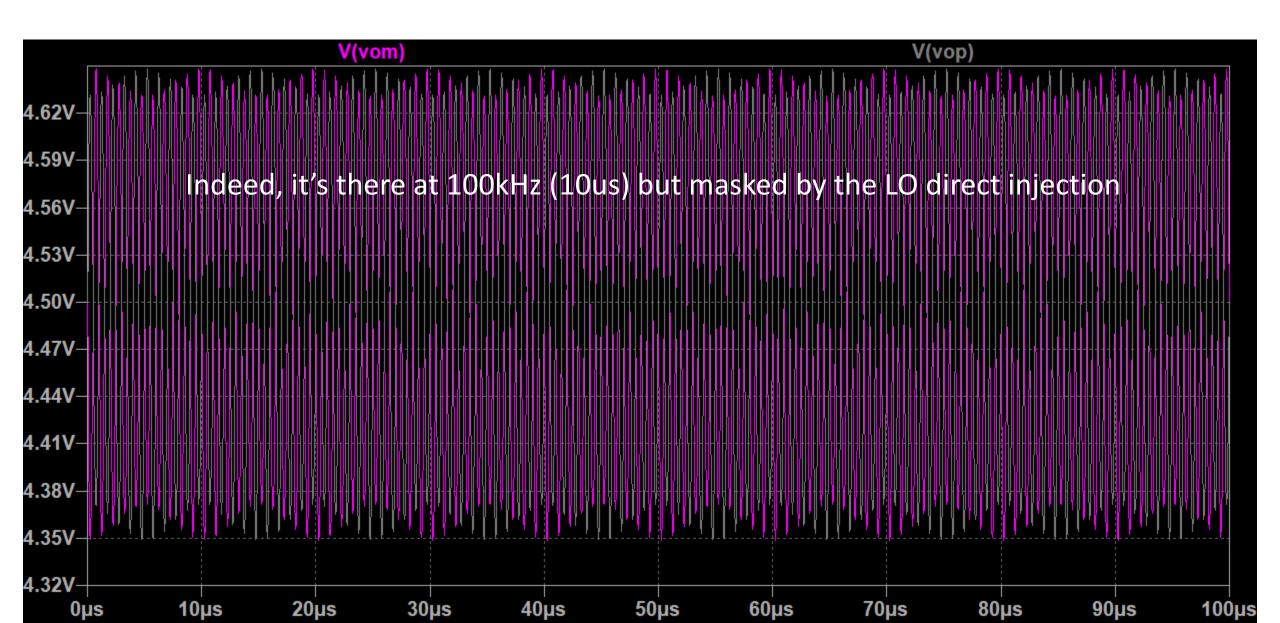
- Sweep -1V<VD<10V, 1st sweep is X-axis
- VS=0, I(VS)>0 (plt)
- VG=1, 2, .., 5V
- VT=0, n=1 =>
 - VDSAT=VG
 - VDG>=0!
- Mirror ok!

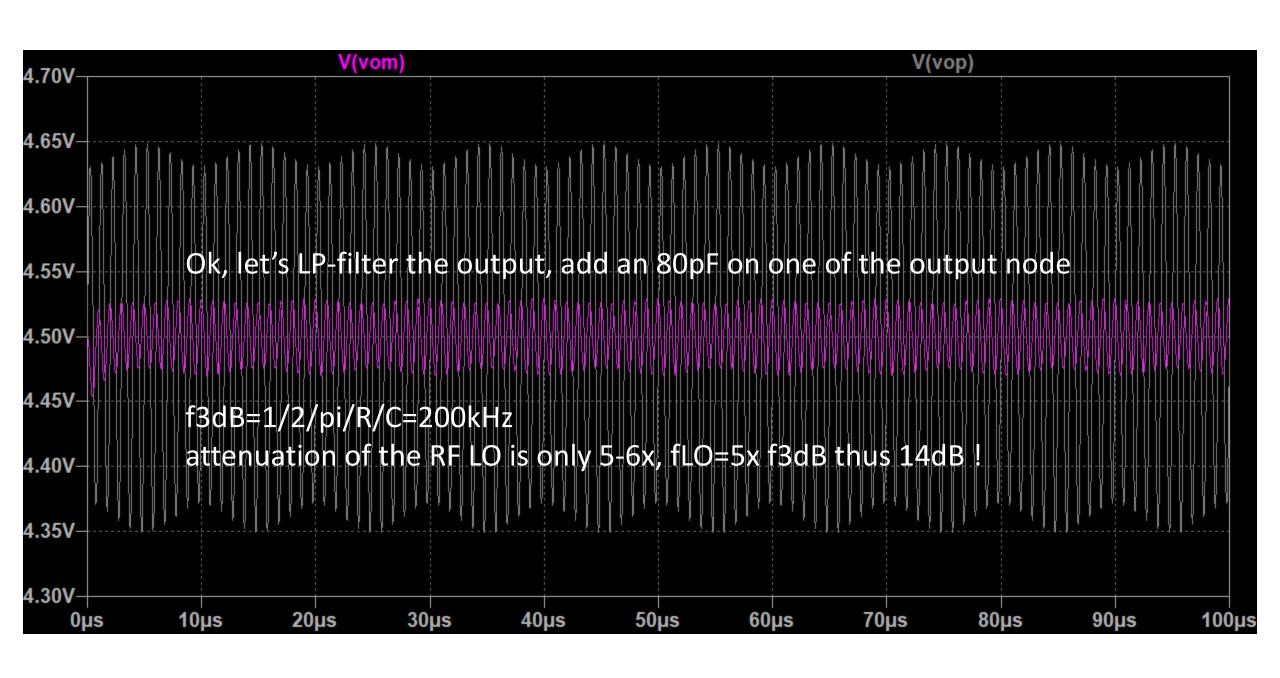


Mixer schematic (use EKV L=0.18um LIB, VDD=1.8V)

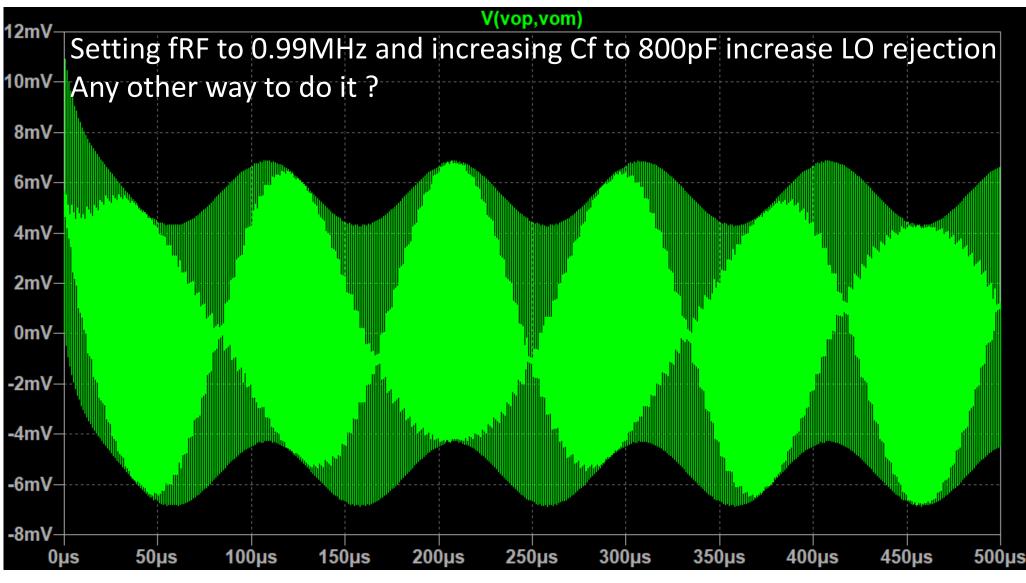




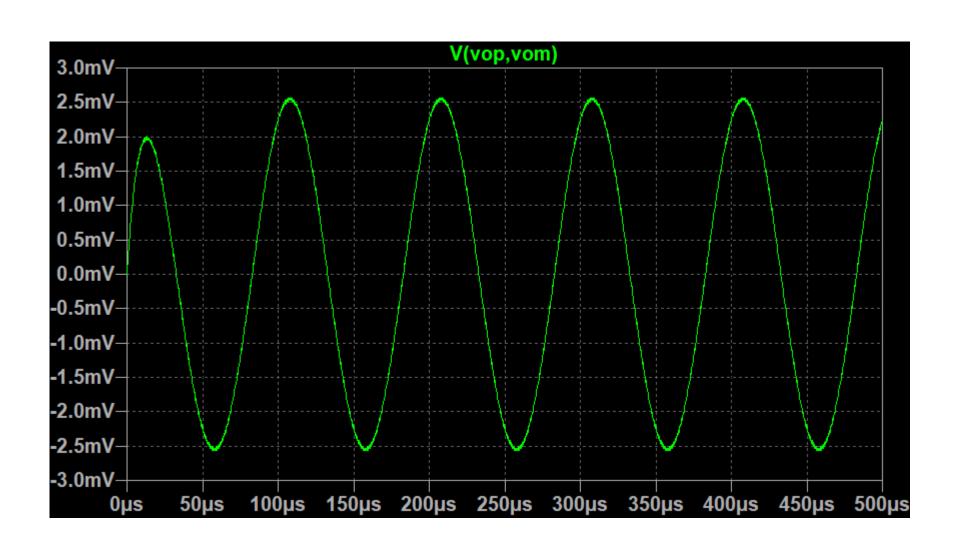




Lowering fIF/fLO ratio

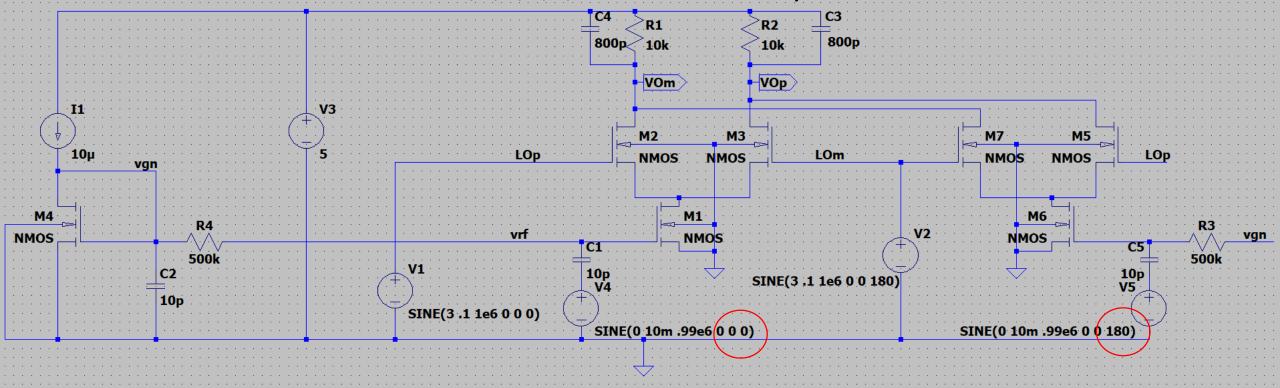


Yes! Double-balanced mixers!



Differential RF input and duplicated diff pair!

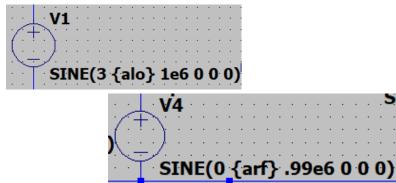
Issue is DC current from RF input MOS M1 which is steered by M2,3 and >> IRF Solution: inject that same DC current on opposite node and AC with -1 gain (hence 180° RF) Same total current and load if M1,2,3,5,6,7 W is reduced by 2x



Replicate that structure and vary RF, LO swings to extract gain, compression (©?)

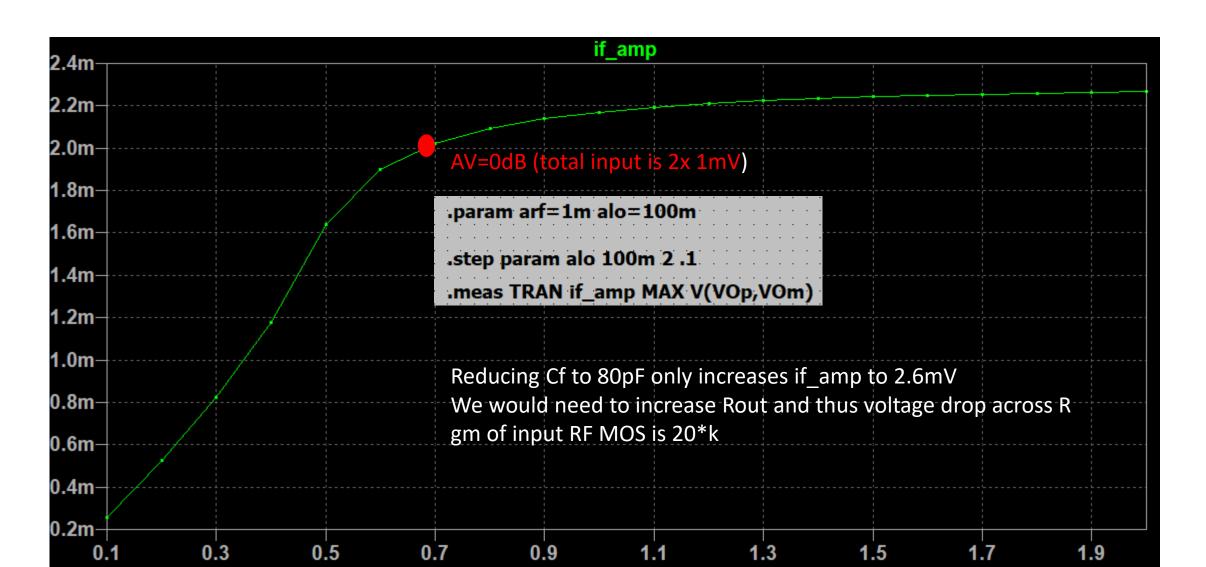
Check the .measure help in LTSpice or use below syntax directives

```
.PARAM arf=10m alo=100m
.step param arf list 1m 2m 4m 8m 16m 32m 64m 128m 256m 512m
.step param alo list 100m 200m 400m 800m 1.6
.meas TRAN if_amp MAX V(VOp,VOm)
```

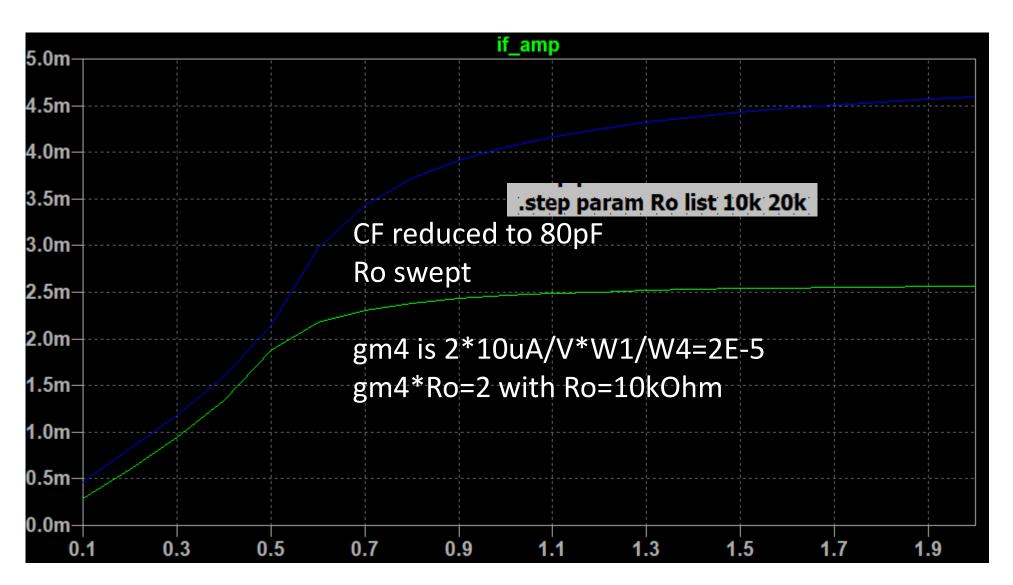


- Select View -> Spice Error Log
- Right clik inside window
- Select Plot stepped meas data Measurement: if_amp

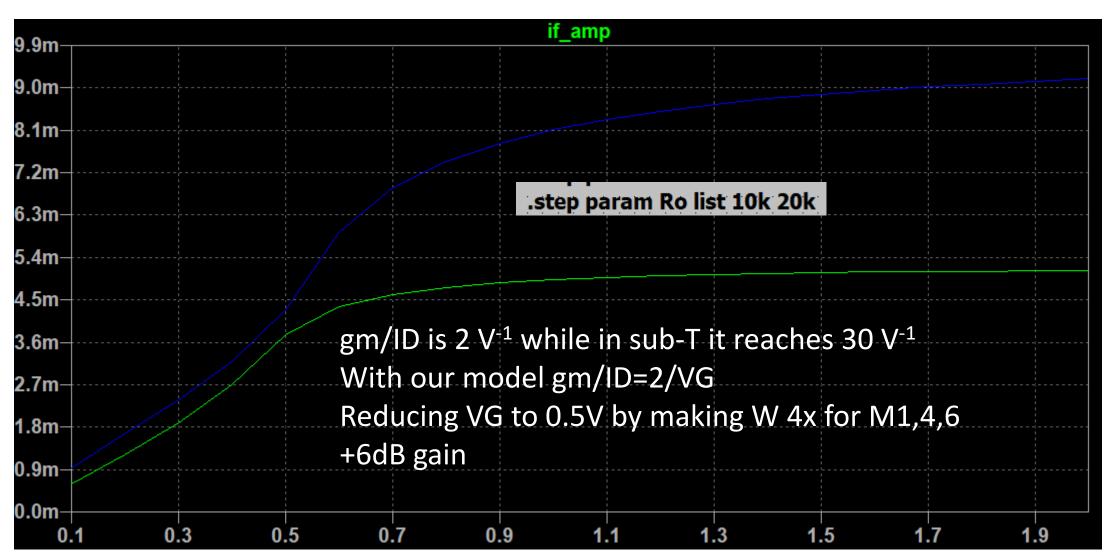
Gain as a function of LO swing

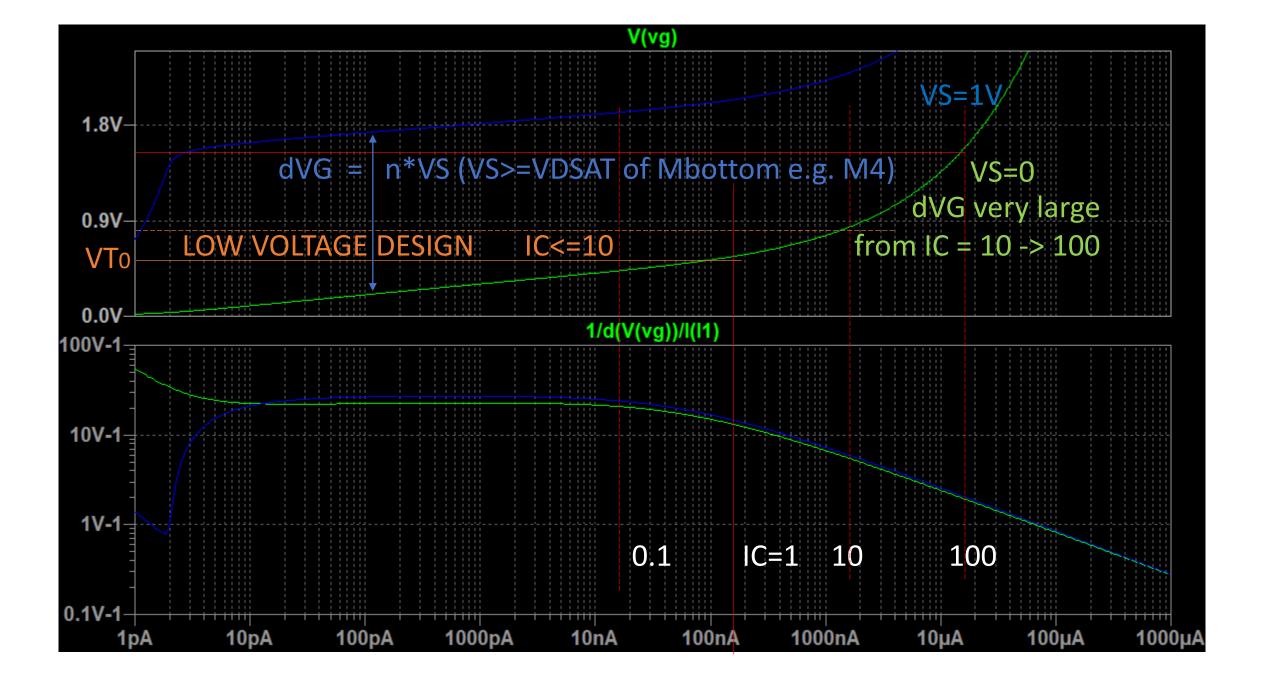


Doubling Ro indeed does increase our gain!



Changing gm/ID (to be updated with EKV!)





Exercises

- Try to vary the W & L of MOS to vary IC
 - AD(S) is drain, source area, PD(S) perimeter
 - AD(S)=W*1u=1p for W=1u; PD(S)=2W+2*1u
 - You could go with L=.1u to limit cap, likely no effect modelled
 - Try to verify cst W/L curves to check this, plot ID, gn/ID, ...
- Study compression of gain especially as you get closer to sub-T
- Try to modulate RF in amplitude or in frequency (fRF=fLO+-10kHz)
 - You may use switches with two voltage sources
 - And look at transient waveforms
- What do you conclude?